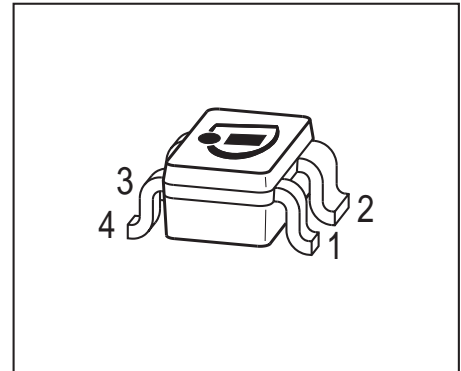


NPN Silicon RF Transistor*

- For low noise, high-gain broadband amplifiers at collector currents from 2 mA to 30 mA
- $f_T = 8$ GHz, $F = 0.9$ dB at 900 MHz
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



* Short term description



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP183W	RHs	1=E	2=C	3=E	4=B	-	-	SOT343

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	12	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	65	mA
Base current	I_B	5	
Total power dissipation ²⁾ $T_S \leq 58$ °C	P_{tot}	450	mW
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ³⁾	R_{thJS}	≤ 205	K/W

¹⁾Pb-containing package may be available upon special request

²⁾ T_S is measured on the collector lead at the soldering point to the pcb

³⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	12	-	-	V
Collector-emitter cutoff current $V_{CE} = 20 \text{ V}, V_{BE} = 0$	I_{CES}	-	-	100	μA
Collector-base cutoff current $V_{CB} = 10 \text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1 \text{ V}, I_C = 0$	I_{EBO}	-	-	1	μA
DC current gain- $I_C = 15 \text{ mA}, V_{CE} = 8 \text{ V}, \text{ pulse measured}$	h_{FE}	70	100	140	-

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

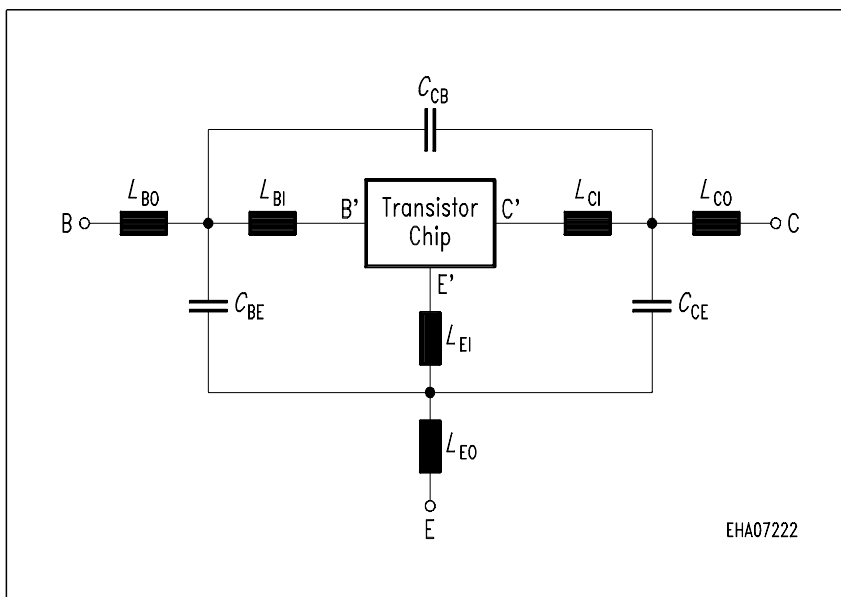
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 25\text{ mA}$, $V_{CE} = 8\text{ V}$, $f = 500\text{ MHz}$	f_T	6	8	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	0.34	0.54	pF
Collector emitter capacitance $V_{CE} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	0.27	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	1.1	-	
Noise figure $I_C = 5\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	F	-	0.9 1.4	-	dB
Power gain, maximum stable ¹⁾ $I_C = 15\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 900\text{ MHz}$	G_{ms}	-	22	-	dB
Power gain, maximum available ¹⁾ $I_C = 15\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$	G_{ma}	-	15.5	-	dB
Transducer gain $I_C = 15\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\ \Omega$, $f = 900\text{ MHz}$ $f = 1.8\text{ MHz}$	$ S_{21e} ^2$	-	17.5 11.5	-	dB

¹⁾ $G_{ma} = |S_{21e} / S_{12e}| (k - (k^2 - 1)^{1/2})$, $G_{ms} = |S_{21} / S_{12}|$

SPICE Parameter (Gummel-Poon Model, Berkley-SPICE 2G.6 Syntax):
Transistor Chip Data:

IS =	1.0345	fA	BF =	115.98	-	NF =	0.80799	-
VAF =	14.772	V	IKF =	0.14562	A	ISE =	16.818	fA
NE =	1.2149	-	BR =	10.016	-	NR =	0.99543	-
VAR =	3.4276	V	IKR =	0.013483	A	ISC =	1.3559	fA
NC =	0.85331	-	RB =	2.5426	Ω	IRB =	0.43801	mA
RBM =	1.0112	Ω	RE =	1.3435	-	RC =	0.20486	Ω
CJE =	23.077	fF	VJE =	1.0792	V	MJE =	0.45354	-
TF =	22.746	ps	XTF =	0.36823	-	VTF =	0.50905	V
ITF =	1.8773	mA	PTF =	0	deg	CJC =	460.11	fF
VJC =	1.1967	V	MJC =	0.3	-	XCJC =	0.053823	-
TR =	1.0553	ns	CJS =	0	fF	VJS =	0.75	V
MJS =	0	-	XTB =	0	-	EG =	1.11	eV
XTI =	3	-	FC =	0.54852	-	TNOM	300	K

All parameters are ready to use, no scaling is necessary. Extracted on behalf of Infineon Technologies AG by: Institut für Mobil- und Satellitentechnik (IMST)

Package Equivalent Circuit:


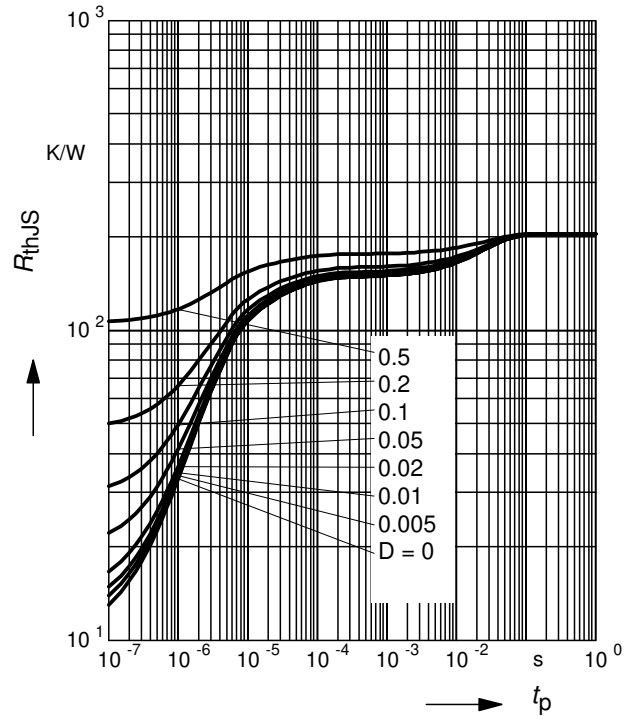
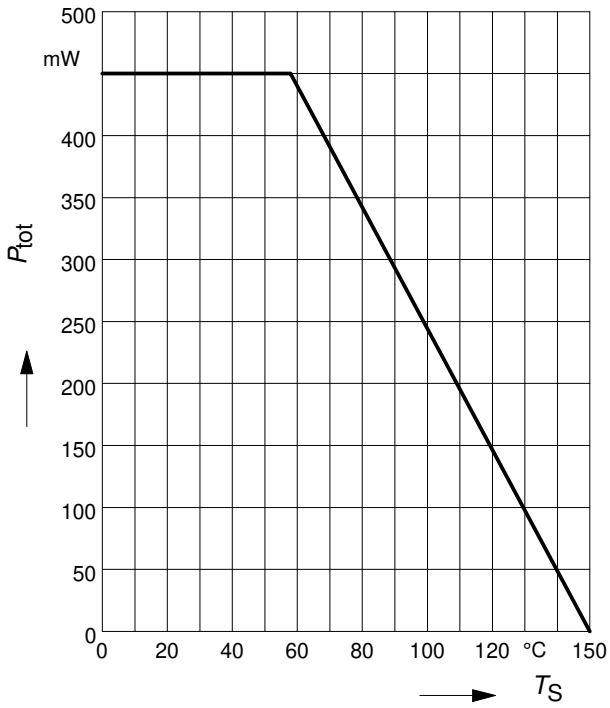
L_{BI} =	0.43	nH
L_{BO} =	0.47	nH
L_{EI} =	0.26	nH
L_{EO} =	0.12	nH
L_{CI} =	0.06	nH
L_{CO} =	0.36	nH
C_{BE} =	68	fF
C_{CB} =	46	fF
C_{CE} =	232	fF

Valid up to 6GHz

For examples and ready to use parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies CD-ROM or see Internet: <http://www.infineon.com>

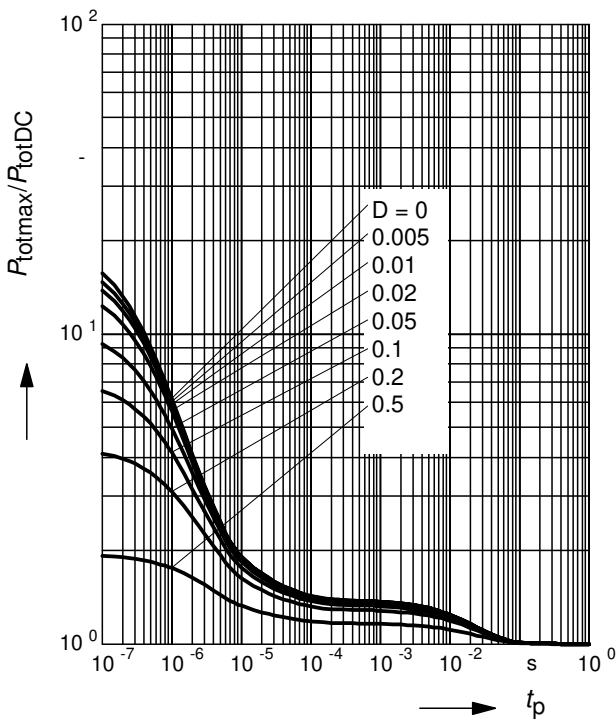
Total power dissipation $P_{tot} = f(T_S)$

Permissible Pulse Load $R_{thJS} = f(t_p)$



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$



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